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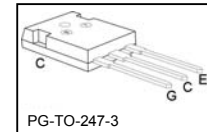
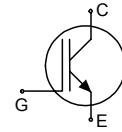
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### Low Loss IGBT in TrenchStop® and Fieldstop technology

- Short circuit withstand time – 10µs
- Designed for :
  - Frequency Converters
  - Uninterrupted Power Supply
- TrenchStop® and Fieldstop technology for 1200 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
- NPT technology offers easy parallel switching capability due to positive temperature coefficient in  $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Qualified according to JEDEC<sup>1</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Marking Code	Package
IGW08T120	1200V	8A	1.7V	150°C	G08T120	PG-TO-247-3

#### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1200	V
DC collector current	$I_C$	16	A
$T_C = 25^\circ C$		8	
$T_C = 100^\circ C$			
Pulsed collector current, $t_p$ limited by $T_{j,max}$	$I_{Cpuls}$	24	
Turn off safe operating area	-	24	
$V_{CE} \leq 1200V, T_j \leq 150^\circ C$			
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Short circuit withstand time <sup>2)</sup>	$t_{SC}$	10	µs
$V_{GE} = 15V, V_{CC} \leq 1200V, T_j \leq 150^\circ C$			
Power dissipation	$P_{tot}$	70	W
$T_C = 25^\circ C$			
Operating junction temperature	$T_j$	-40...+150	°C
Storage temperature	$T_{stg}$	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1</sup> J-STD-020 and JEDEC-022

<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		1.7	K/W
Thermal resistance, junction – ambient	$R_{thJA}$		40	

**Electrical Characteristic, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.5mA$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=8A$ $T_j=25\text{ }^\circ\text{C}$ $T_j=125\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$	-	1.7	2.2	
			-	2.0	-	
			-	2.2	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=0.3mA, V_{CE}=V_{GE}$	5.0	5.8	6.5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V,$ $V_{GE}=0V$ $T_j=25\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$	-	-	0.2	mA
			-	-	2.0	
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=8A$	-	5	-	S
Integrated gate resistor	$R_{Gint}$		none			$\Omega$

**Dynamic Characteristic**

Input capacitance	$C_{iss}$	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$	-	600	-	pF
Output capacitance	$C_{oss}$		-	36	-	
Reverse transfer capacitance	$C_{riss}$		-	28	-	
Gate charge	$Q_{Gate}$	$V_{CC}=960V, I_C=8A$ $V_{GE}=15V$	-	53	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	13	-	nH
Short circuit collector current <sup>1)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s$ $V_{CC}=600V,$ $T_j=25\text{ }^\circ\text{C}$	-	48	-	A

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

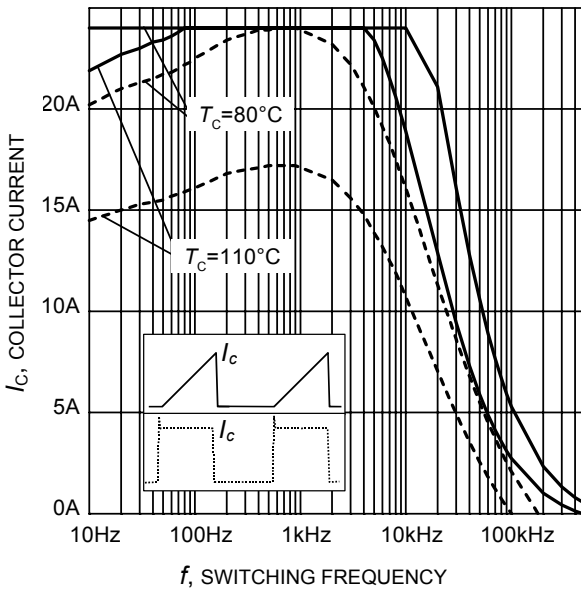
**Switching Characteristic, Inductive Load, at  $T_j=25^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$ , $V_{CC}=600\text{V}$ , $I_C=8\text{A}$ , $V_{GE}=-15/15\text{V}$ , $R_G=81\Omega$ , $L_{\sigma}^{2)}=180\text{nH}$ , $C_{\sigma}^{2)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	40	-	ns
Rise time	$t_r$		-	23	-	
Turn-off delay time	$t_{d(off)}$		-	450	-	
Fall time	$t_f$		-	70	-	mJ
Turn-on energy	$E_{on}$		-	0.67	-	
Turn-off energy	$E_{off}$		-	0.7	-	
Total switching energy	$E_{ts}$		-	1.37	-	

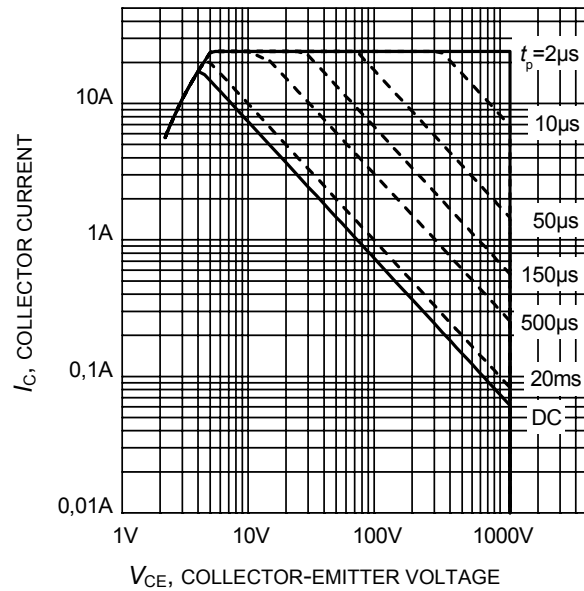
**Switching Characteristic, Inductive Load, at  $T_j=150^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$ , $V_{CC}=600\text{V}$ , $I_C=8\text{A}$ , $V_{GE}=-15/15\text{V}$ , $R_G=81\Omega$ , $L_{\sigma}^{2)}=180\text{nH}$ , $C_{\sigma}^{2)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	40	-	ns
Rise time	$t_r$		-	26	-	
Turn-off delay time	$t_{d(off)}$		-	570	-	
Fall time	$t_f$		-	140	-	mJ
Turn-on energy	$E_{on}$		-	1.08	-	
Turn-off energy	$E_{off}$		-	1.2	-	
Total switching energy	$E_{ts}$		-	2.28	-	

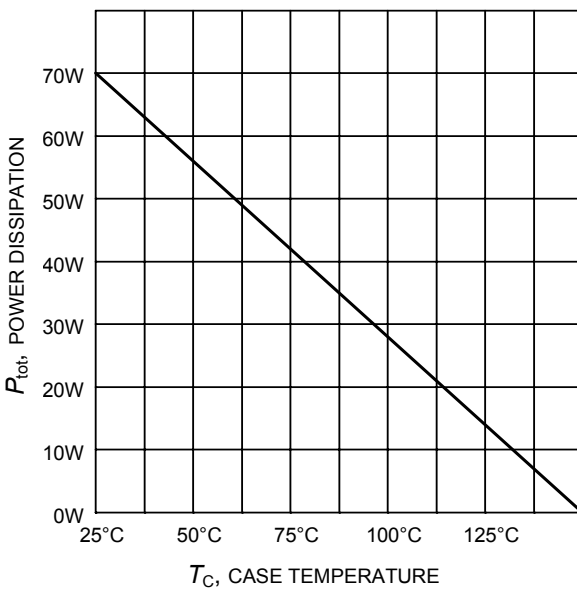
<sup>2)</sup> Leakage inductance  $L_{\sigma}$  and Stray capacity  $C_{\sigma}$  due to dynamic test circuit in Figure E.



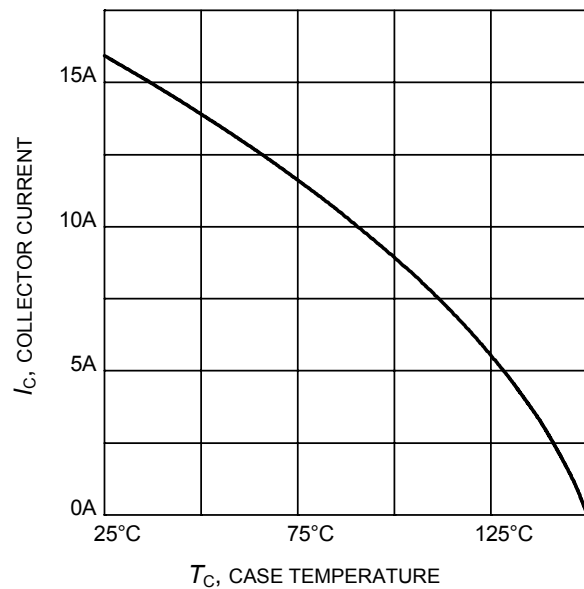
**Figure 1. Collector current as a function of switching frequency**  
 ( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 600\text{V}$ ,  
 $V_{GE} = 0/+15\text{V}$ ,  $R_G = 81\Omega$ )



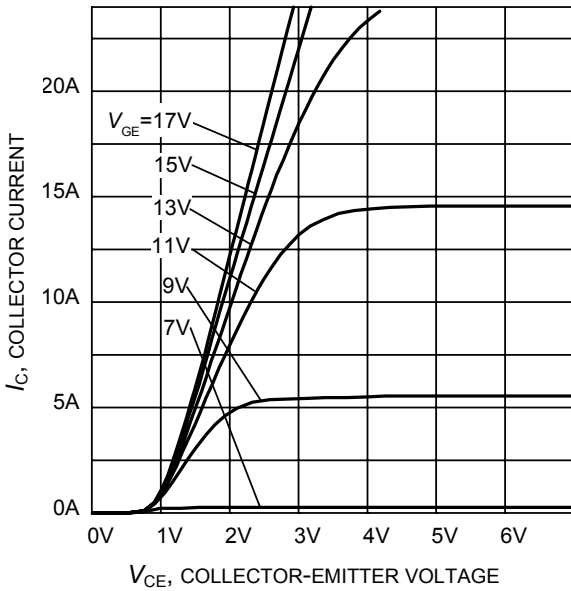
**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  
 $T_j \leq 150^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$ )



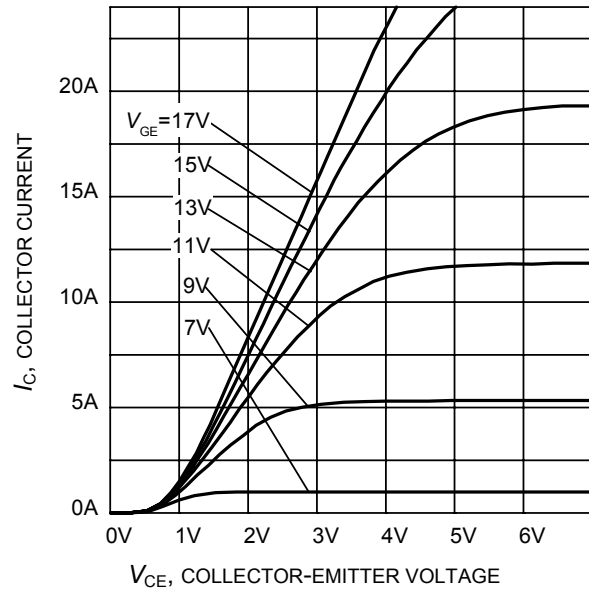
**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 150^\circ\text{C}$ )



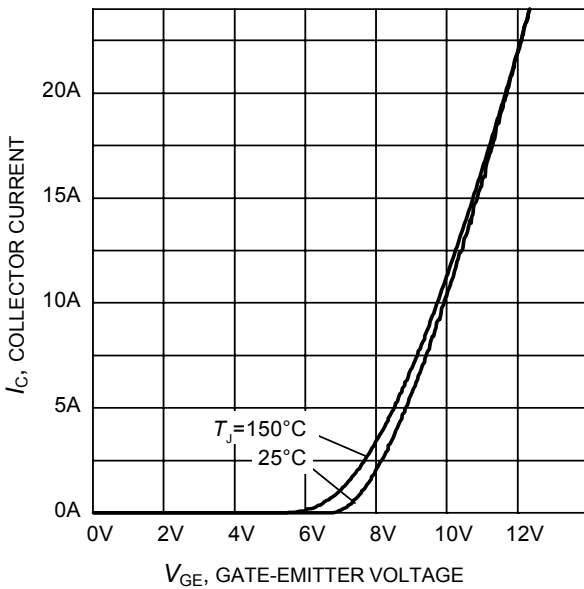
**Figure 4. Collector current as a function of case temperature**  
 ( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



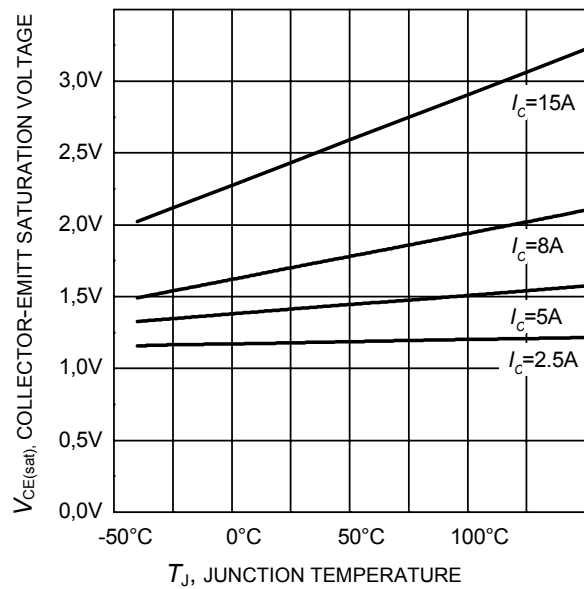
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



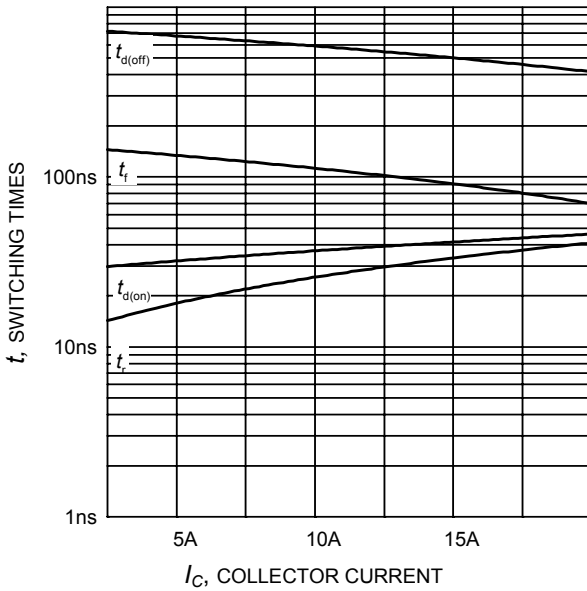
**Figure 6. Typical output characteristic**  
( $T_j = 150^\circ\text{C}$ )



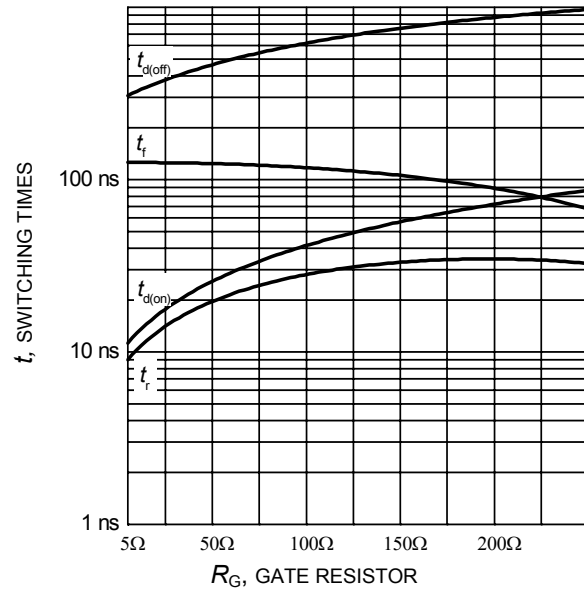
**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 20\text{V}$ )



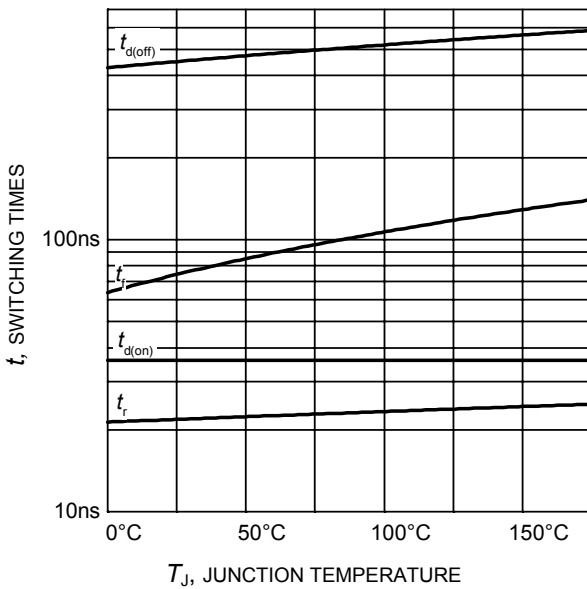
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



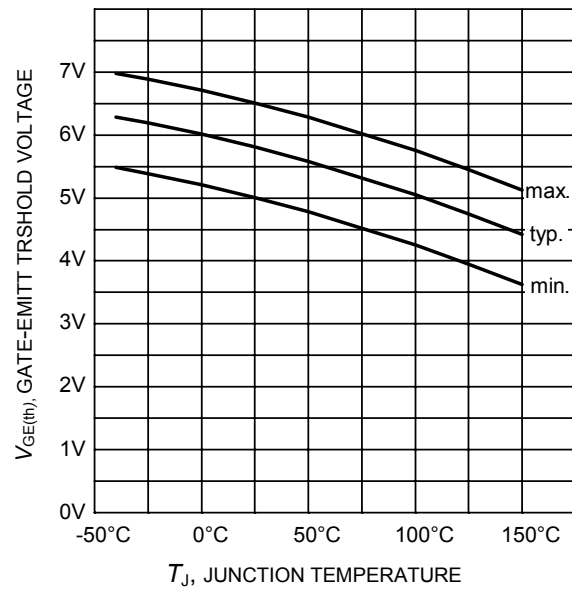
**Figure 9. Typical switching times as a function of collector current**  
 (inductive load,  $T_J=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=81\Omega$ , Dynamic test circuit in Figure E)



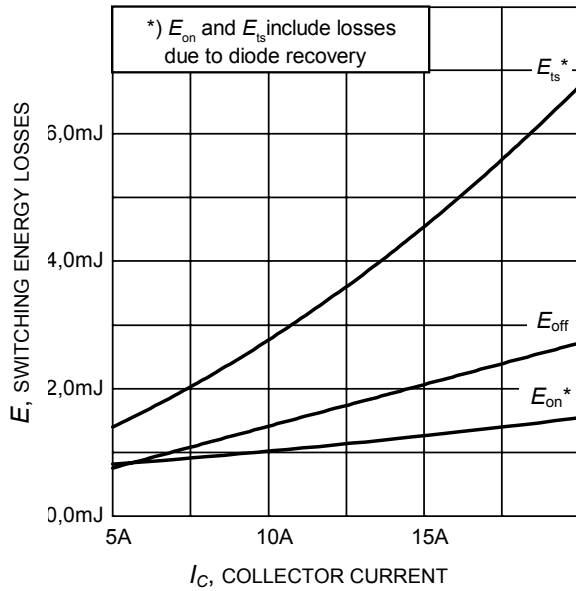
**Figure 10. Typical switching times as a function of gate resistor**  
 (inductive load,  $T_J=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=8\text{A}$ , Dynamic test circuit in Figure E)



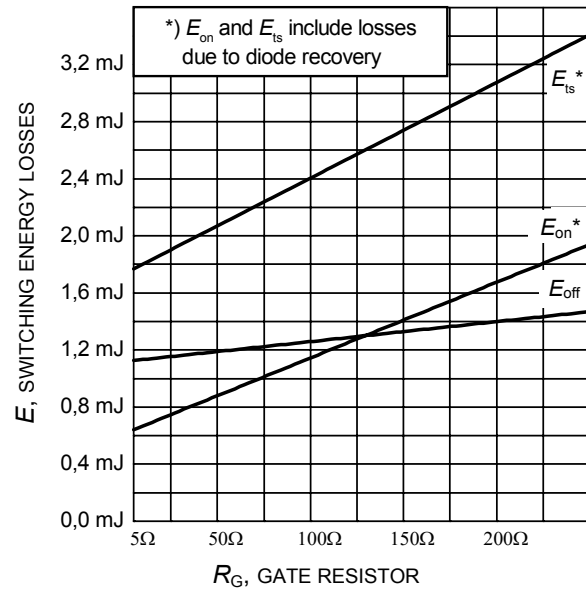
**Figure 11. Typical switching times as a function of junction temperature**  
 (inductive load,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=8\text{A}$ ,  $R_G=81\Omega$ , Dynamic test circuit in Figure E)



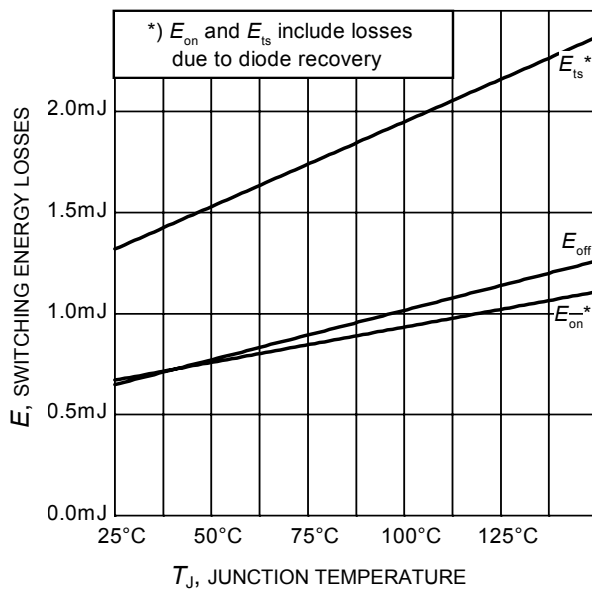
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
 ( $I_C = 0.3\text{mA}$ )



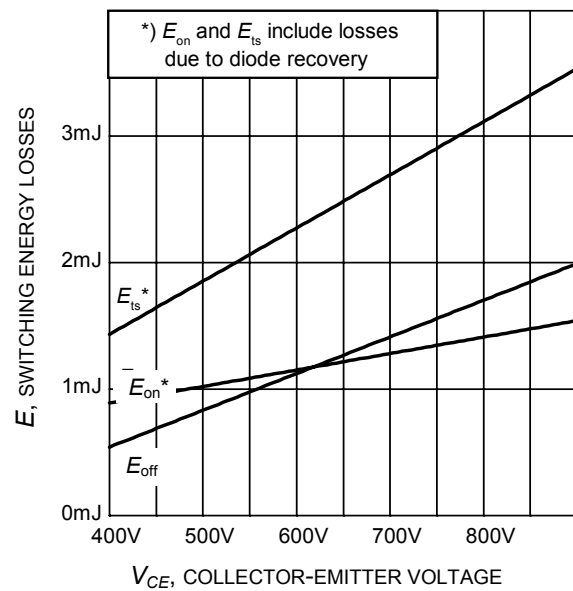
**Figure 13. Typical switching energy losses as a function of collector current**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=81\Omega$ , Dynamic test circuit in Figure E)



**Figure 14. Typical switching energy losses as a function of gate resistor**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=8\text{A}$ , Dynamic test circuit in Figure E)

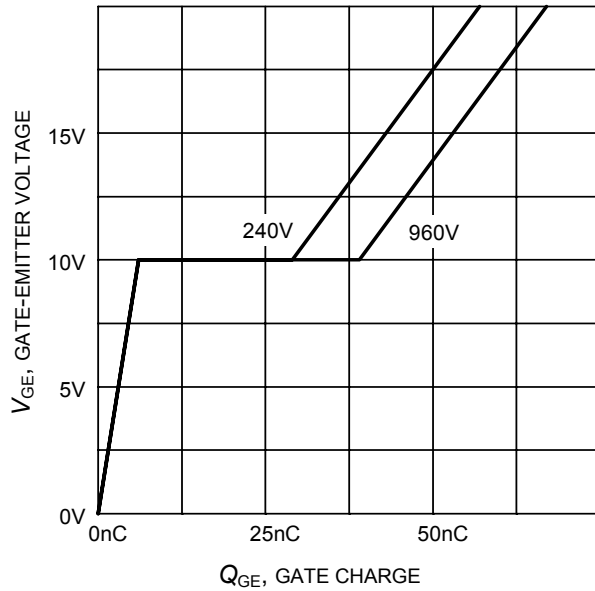


**Figure 15. Typical switching energy losses as a function of junction temperature**  
 (inductive load,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=8\text{A}$ ,  $R_G=81\Omega$ , Dynamic test circuit in Figure E)

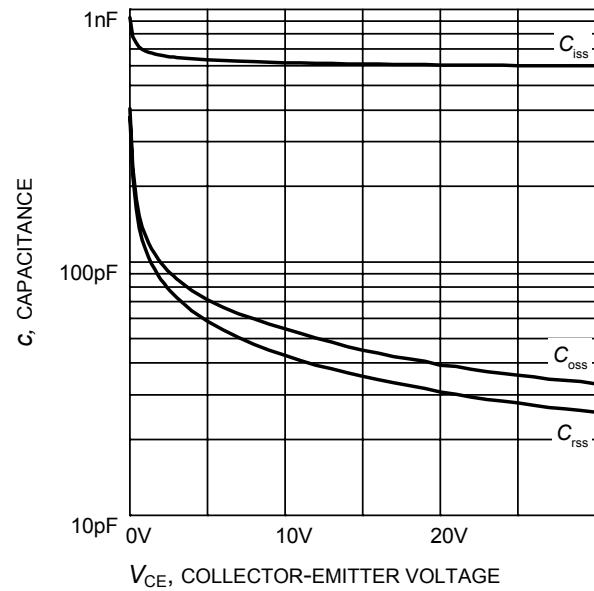


**Figure 16. Typical switching energy losses as a function of collector emitter voltage**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=8\text{A}$ ,  $R_G=81\Omega$ , Dynamic test circuit in Figure E)

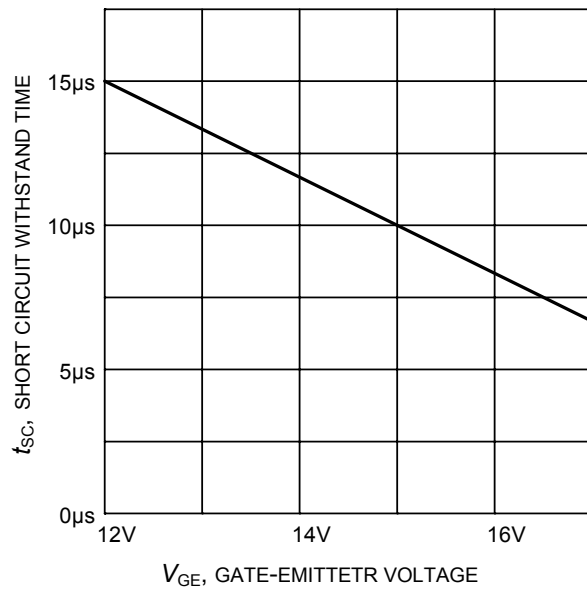




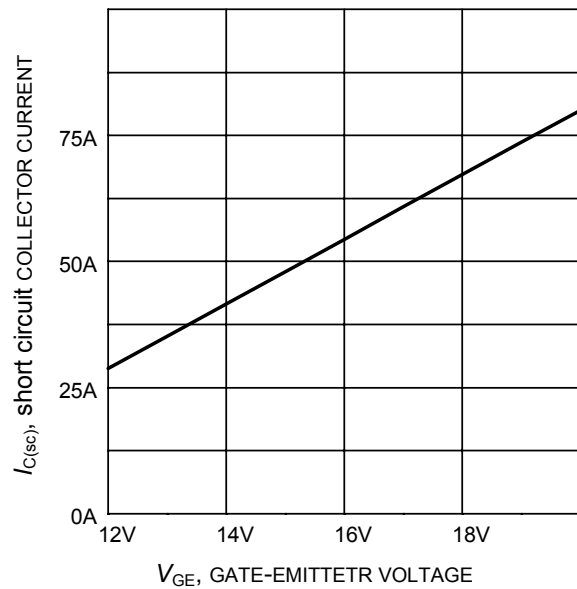
**Figure 17. Typical gate charge**  
( $I_C=8\text{ A}$ )



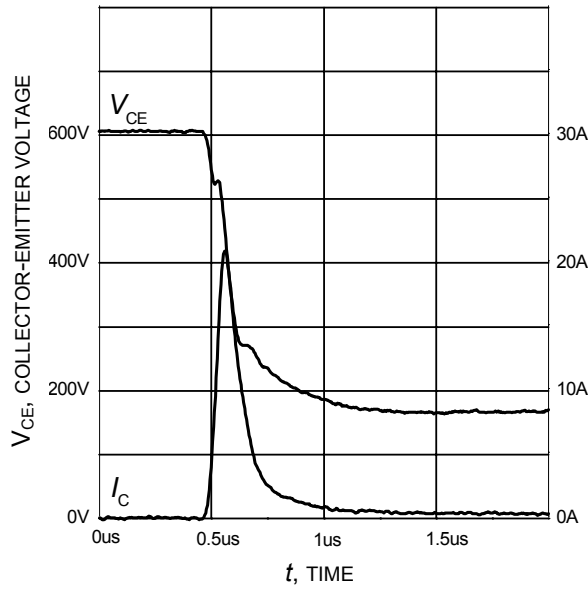
**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0\text{V}$ ,  $f=1\text{ MHz}$ )



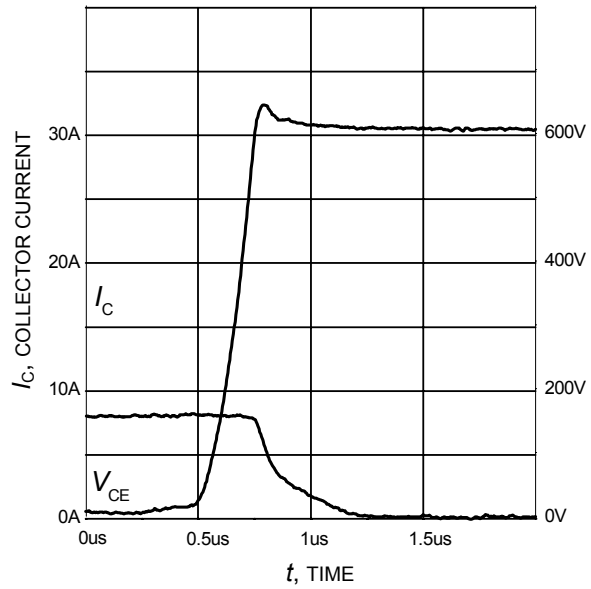
**Figure 19. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE}=600\text{V}$ , start at  $T_J=25^\circ\text{C}$ )



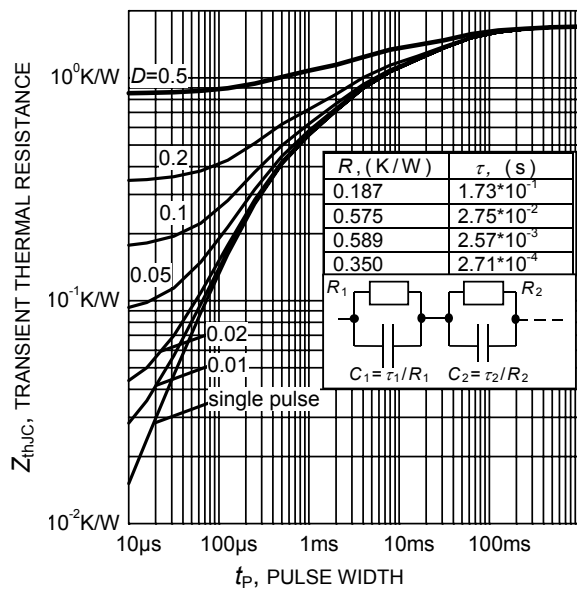
**Figure 20. Typical short circuit collector current as a function of gate-emitter voltage**  
( $V_{CE} \leq 600\text{V}$ ,  $T_J \leq 150^\circ\text{C}$ )



**Figure 21. Typical turn on behavior**  
 $(V_{GE}=0/15V, R_G=81\Omega, T_J = 150^\circ C,$   
 Dynamic test circuit in Figure E)

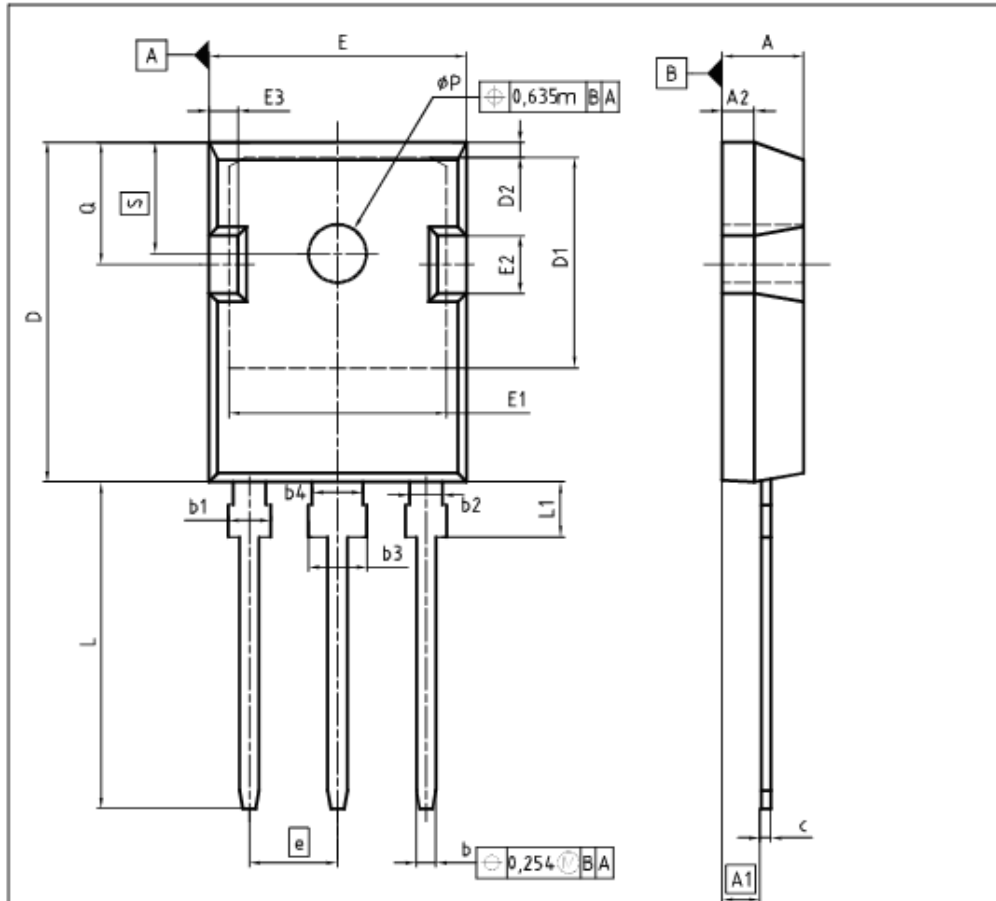


**Figure 22. Typical turn off behavior**  
 $(V_{GE}=15/0V, R_G=81\Omega, T_J = 150^\circ C,$   
 Dynamic test circuit in Figure E)



**Figure 23. IGBT transient thermal resistance**  
 $(D = t_p / T)$

TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
φP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

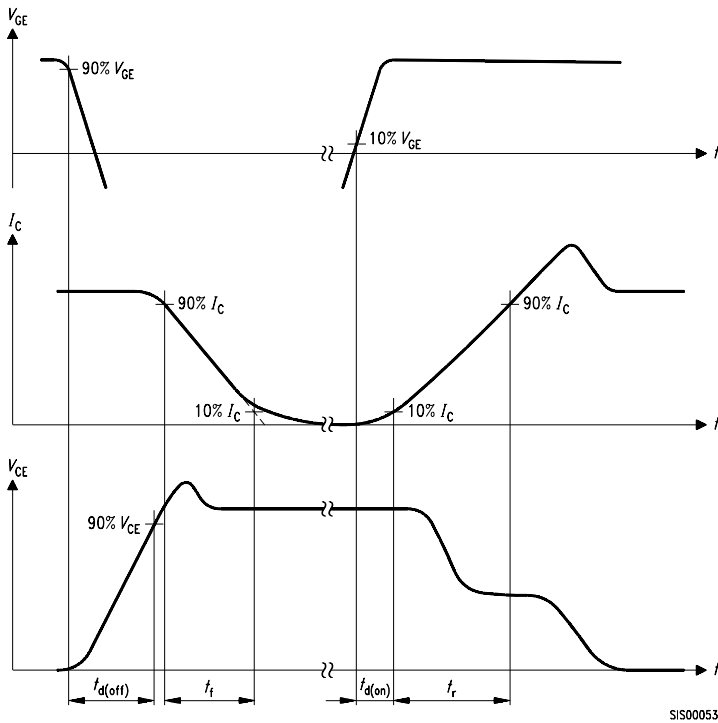
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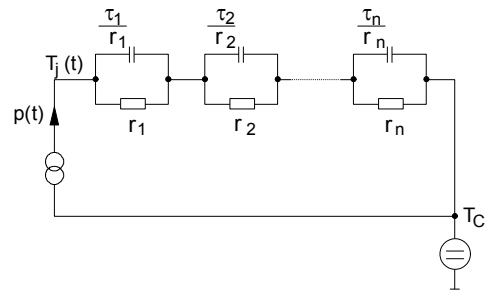
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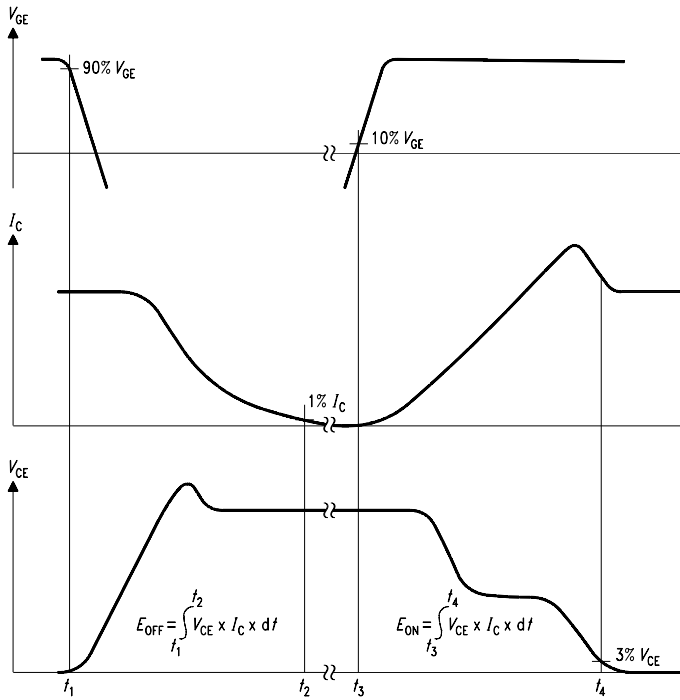


**Figure A. Definition of switching times**

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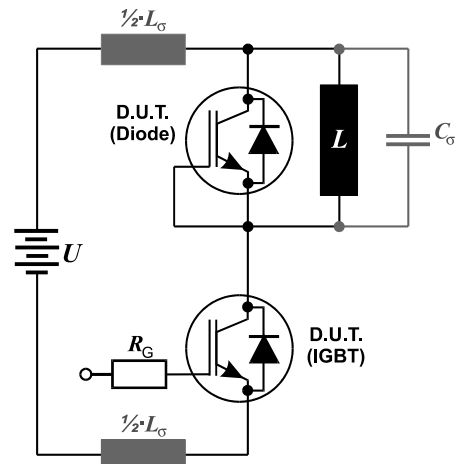


**Figure D. Thermal equivalent circuit**



**Figure B. Definition of switching losses**

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**Figure E. Dynamic test circuit**  
Leakage inductance  $L_\sigma = 180\text{nH}$   
and Stray capacity  $C_\sigma = 39\text{pF}$ .

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